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14-Bit Binary Counter

The MC14020B 14-stage binary counter is constructed with MOS P-Channel and N-Channel enhancement mode devices in a single monolithic structure. This part is designed with an input wave shaping circuit and 14 stages of ripple-carry binary counter. The device advances the count on the negative-going edge of the clock pulse. Applications include time delay circuits, counter controls, and frequency-dividing circuits.

Features

- Fully Static Operation
- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low–power TTL Loads or One Low–power Schottky TTL Load Over the Rated Temperature Range
- Buffered Outputs Available from stages 1 and 4 thru 14
- Common Reset Line
- Pin-for-Pin Replacement for CD4020B
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V _{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient)	–0.5 to V _{DD} + 0.5	V
I _{in} , I _{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P _D	Power Dissipation, per Package (Note 1)	500	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in} \text{ or } V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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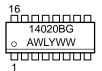


SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

PIN ASSIGNMENT

Q12 [1●		V _{DD}
Q13 [2	15	Q11
Q14 [3	14	Q10
Q6 [4	13] Q8
Q5 [5	12] Q9
Q7 [6	11	R
Q4 [7	10] C
V _{SS} [8	9] Q1

MARKING DIAGRAMS



SOIC-16



TSSOP-16

A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or = Pb-Free Indicator

(Note: Microdot may be in either location)

ORDERING INFORMATION

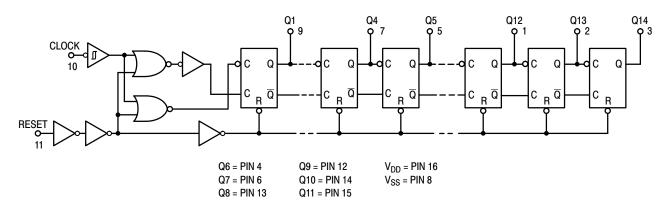
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

TRUTH TABLE

Clock	Reset	Output State
	0	No Change
	0	Advance to Next State
X	1	All Outputs are Low

X = Don't Care

LOGIC DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
MC14020BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14020BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14020BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
MC14020BDTG	TSSOP-16 (Pb-Free)	96 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

				-55	5°C		25°C		12	5°C	
Characteristic		Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05		0 0 0	0.05 0.05 0.05		0.05 0.05 0.05	Vdc
V _{in} = 0 or V _{DD}	"1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage (V _O = 4.5 or 0.5 Vdc) (V _O = 9.0 or 1.0 Vdc) (V _O = 13.5 or 1.5 Vdc)	"0" Level	V _{IL}	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V _{IH}	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	Vdc
Output Drive Current $ (V_{OH} = 2.5 \text{ Vdc}) $ $ (V_{OH} = 4.6 \text{ Vdc}) $ $ (V_{OH} = 9.5 \text{ Vdc}) $ $ (V_{OH} = 13.5 \text{ Vdc}) $	Source	I _{OH}	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - -	-1.7 -0.36 -0.9 -2.4	- - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current		I _{in}	15	_	±0.1	-	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V _{in} = 0)		C _{in}	-	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package)		I _{DD}	5.0 10 15	- - -	5.0 10 20	- - -	0.005 0.010 0.015	5.0 10 20	- - -	150 300 600	μAdc
Total Supply Current (Note: (Dynamic plus Quiescei Per Package) (C _L = 50 pF on all output buffers switching)	nt,	Ι _Τ	5.0 10 15			$I_T = (0$).42 μΑ/kHz)i).85 μΑ/kHz)i .43 μΑ/kHz)i	f + I _{DD}			μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μA (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.001.

^{3.} The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

SWITCHING CHARACTERISTICS (Note 5) (C $_L$ = 50 pF, T_A = $25^{\circ}C)$

Characteristic	Symbol	V _{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time $t_{TLH}, t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$ $t_{TLH}, t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$ $t_{TLH}, t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$	t _{TLH} , t _{THL}	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time Clock to Q1 $t_{PHL}, t_{PLH} = (1.7 \text{ ns/pF}) C_L + 175 \text{ ns}$ $t_{PHL}, t_{PLH} = (0.66 \text{ ns/pF}) C_L + 82 \text{ ns}$ $t_{PHL}, t_{PLH} = (0.5 \text{ ns/pF}) C_L + 55 \text{ ns}$	t _{PLH} , t _{PHL}	5.0 10 15	- - -	260 115 80	520 230 160	ns
Clock to Q14 t_{PHL} , t_{PLH} – (1.7 ns/pF) C_L + 1735 ns t_{PHL} , t_{PLH} = (0.66 ns/pF) C_L + 772 ns t_{PHL} , t_{PLH} = (0.5 ns/pF) C_L + 535 ns		5.0 10 15	- - -	1820 805 560	3900 1725 1200	ns
Propagation Delay Time Reset to Q_n $t_{PHL} = (1.7 \text{ ns/pF}) C_L + 285 \text{ ns}$ $t_{PHL} = (0.66 \text{ ns/pF}) C_L + 122 \text{ ns}$ $t_{PHL} = (0.5 \text{ ns/pF}) C_L + 90 \text{ ns}$	t _{PHL}	5.0 10 15	- - -	370 155 115	740 310 230	ns
Clock Pulse Width	t₩H	5.0 10 15	500 165 125	140 55 38	- - -	ns
Clock Pulse Frequency	f _{max}	5.0 10 15	1.0 3.0 4.0	2.0 6.0 8.0	- - -	MHz
Clock Rise and Fall Time	t _{TLH} , t _{THL}	5.0 10 15		No Limit		-
Reset Pulse Width	t _{WL}	5.0 10 15	3000 550 420	320 120 80	- - -	ns
Reset Recovery Time	t _{rec}	5.0 10 15	- - -	65 25 15	130 50 30	ns

^{5.} The formulas given are for the typical characteristics only at 25°C.6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

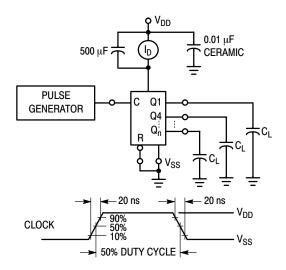


Figure 1. Power Dissipation Test Circuit and Waveform

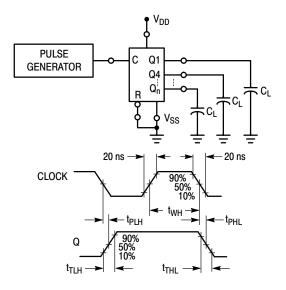


Figure 2. Switching Time Test Circuit and Waveforms

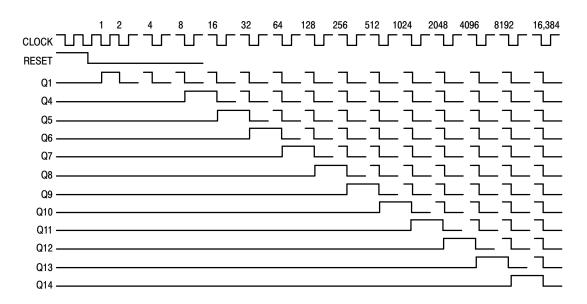
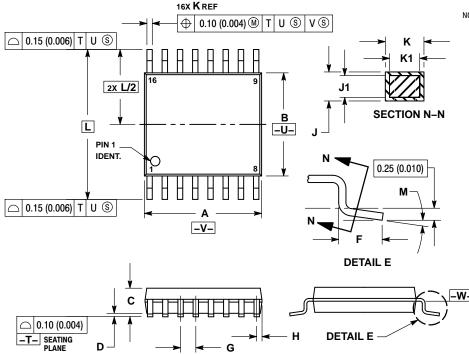


Figure 3. Timing Diagram

PACKAGE DIMENSIONS

TSSOP-16 DT SUFFIX PLASTIC TSSOP PACKAGE CASE 948F ISSUE B



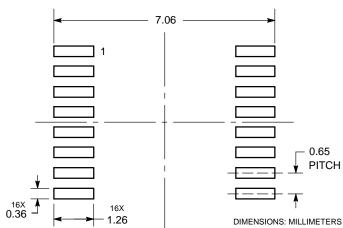
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH.
 PROTRUSIONS OR GATE BURRS. MOLD FLASH OR
 GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER
- SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALLOWABLE TO THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
۲	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
٦	6.40	BSC	0.252	BSC	
М	0°	8 °	n °	8 °	

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.